

# Imaging and manipulating electrons in a 1D quantum dot with Coulomb blockade microscopy

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(Dated: April 23, 2019)

Motivated by the recent experiments by the Westervelt group using a mobile tip to probe the electronic state of quantum dots formed on a segmented nanowire, we study the shifts in Coulomb blockade peak positions as a function of the spatial variation of the tip potential, which can be termed ‘‘Coulomb blockade microscopy’’. We show that if the tip can be brought sufficiently close to the nanowire, one can distinguish a high density electronic liquid state from a Wigner crystal state by microscopy with a weak tip potential. In the opposite limit of a strongly negative tip potential, the potential depletes the electronic density under it and divides the quantum wire into two partitions. There the tip can push individual electrons from one partition to the other, and the Coulomb blockade micrograph can clearly track such transitions. We show that this phenomenon can be used to qualitatively estimate the relative importance of the electron interaction compared to one particle potential and kinetic energies. Finally, we propose that a weak tip Coulomb blockade micrograph focusing on the transition between electron number  $N = 0$  and  $N = 1$  states may be used to experimentally map the one-particle potential landscape produced by impurities and inhomogeneities.

Studies of nanoscale electronic structures hold important promise both as laboratories for few-body, interacting quantum mechanical systems and as technological testbeds for future classical or quantum computing technologies. Novel probe technologies [1, 2] are very important for studying electronic properties in nanoscale systems because they are often beyond the resolution of conventional imaging techniques like optical microscopy, and traditional transport measurements can only measure spatially averaged physical properties such as the conductance or the current. One scanning probe microscopy (SPM) [2] technique utilizes a charged metallic tip to perturb the local electronic density in a nanoelectronic structure and measure the resulting change in transport properties. Using this technique one can obtain spatially resolved measurement of the electronic properties, including the local electron density and, in principle, the wavefunction itself in the case of a one-electron system [3] (see discussions below). This imaging technique has been fruitfully applied to study the flow of ballistic electrons across a range of two dimensional heterostructures.

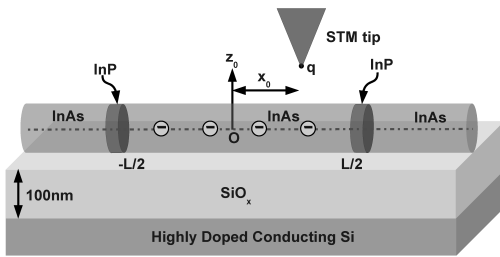


FIG. 1: Schematic geometry of Coulomb blockade microscopy of a quantum wire containing four electrons. When calculating the electron-electron interaction and the electron-tip interaction, we assume that the InP barriers have zero thickness, the InAs wire is infinitely long, and the substrate layers extend to infinity in  $x$  and  $y$  directions.

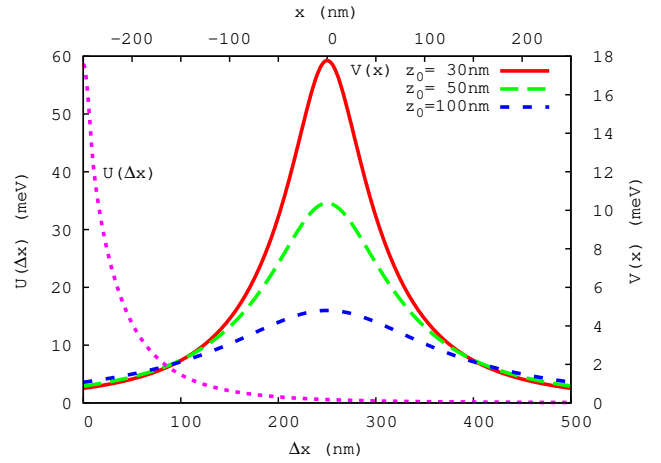


FIG. 2: (Color Online) (Dotted) Interaction potential  $U(\Delta z)$ . (Solid, long and short dashed) Tip  $V(x)$  potentials with a tip charge  $q = e$  and locations  $\vec{r}_0 = (0, 0, z_0)$  where  $z_0 = 30\text{nm}, 50\text{nm}, 100\text{nm}$ .

Recently, a series of experiments [4] applied SPM technique to study quantum wires. In these experiments a segment of an InAs nanowire lying on top of a two dimensional  $\text{SiO}_x$  layer was isolated from the rest of the wire by two short InP layers, forming a one-dimensional quantum dot with lithographically defined boundaries. A negatively charged probe scanned controllably the two dimensional area around the wire and the conductance across the 1D quantum dot was measured as a function of the probe location. Both the voltage of the probe and its height above the surface can also be independently varied. Motivated by these new experimental possibilities, we turn to exact diagonalization techniques to study the conductance response of a few-electron quantum dot as a function of a spatially varied probe potential, in order to illustrate the kind of information that can be extracted in the case of a system of several electrons.

We consider a uniform InAs (dielectric constant  $\epsilon = 15.4$ ) nanowire of radius  $R = 10\text{nm}$ , which lies in vacuum atop a

SiO<sub>x</sub> ( $\epsilon = 3.9$ ) layer 100nm thick, separating it from conducting doped bulk silicon (see Fig. 1). Electrons are modelled as point charges traveling along the center axis of the wire, confined to interval  $-\frac{L}{2} < x < \frac{L}{2}$  by hard walls, representing the InP layers. We consider length  $L$  from 110nm to 500nm. The electron-electron interaction  $U(x_1 - x_2)$  was calculated using the commercial finite-element program Comsol<sup>TM</sup> to solve the classical Poisson equation for a point charge on the axis of an infinite wire above in a substrate with the geometry described in Fig. 1. At short distance  $\Delta x$ , the potential was softened to account for the finite thickness of the electron wavefunction, by replacing  $\Delta x^{-1}$  with  $[(\Delta x)^2 + R^2]^{-1/2}$ . Following the approximation used by Topinka [5], we model the negatively charged probe as a fixed point charge of strength  $q$  at a location  $\vec{r}_0$  relative to the center point of the wire. This gives rise to a one-body potential  $V(x; \vec{r}_0, q)$  for an electron on the wire axis at point  $x$ , which we again obtain by solving the Poisson equation (results are shown in Fig. 2).

In this paper, we diagonalize the exact 1D many-body Hamiltonian with the Lanczos method [6] for up to electron number  $N = 4$ :

$$-\frac{\hbar^2}{2m^*} \nabla^2 \Psi + \sum_{i=1}^N V(x_i; \vec{r}_0, q) \Psi + \sum_{i=1}^N \sum_{j=1}^{i-1} U(x_i, x_j) \Psi = E \Psi, \quad (1)$$

where  $\Psi$  is the full many-body wavefunction, depending on the position  $x_i$  and spin  $\sigma_i$  of the electrons. To connect to the experimentally observable variables, we consider the Coulomb blockade peak *positions* of the transition from  $(N-1)$  to  $N$  electron ground states. The conductance through the quantum wire is maximum when a backgate voltage, controlling the overall chemical potential difference between the leads and the wire, is equal to the ground state energy difference between the two states in question  $V_g = \Delta E = E_N - E_{N-1}$ . We probe the electronic states in the quantum wire through the dependence of  $\Delta E$  on the tip position  $\vec{r}_0$  and potential strength  $q$ . An interesting set of spatially resolved information about the electrons in the wire can be extracted from this function, and we call this method ‘‘Coulomb blockade microscopy’’. It is a special application of the ‘‘scanning probe microscopy’’ developed by the Westervelt group [2]. In calculations in this paper we focus on the transition from  $N = 3$  to  $N = 4$  electrons, but most of our conclusions are easily generalizable to other ground state transitions. Finally, we note that for four non-interacting electrons with spin in a wire of radius  $R = 10\text{nm}$ , when the dot length  $L > L_m = 18.2\text{nm}$ , the lowest four single particle energy levels are all longitudinal modes. The shortest wire length we consider in this paper  $L = 110\text{nm} \gg L_m$ , and we expect the wires under consideration can be well approximated as strictly 1D.

In the absence of a probe potential  $V$ , both the  $N = 3$  and  $N = 4$  wires the electronic density profile  $\rho(x)$  undergoes a crossover as a function of  $L$  from a liquid state characterized by a  $2k_F$  Friedel oscillations to a quasi-Wigner crystal state characterized by a  $4k_F$  density oscillation. For a wire of radius  $R = 10\text{nm}$ , the crossover happens around den-

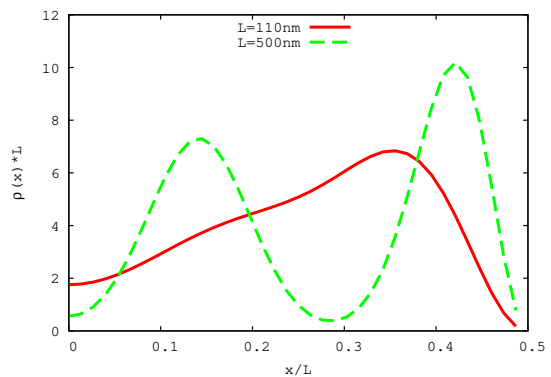


FIG. 3: (Color Online) Electronic densities for a  $L = 110\text{nm}$  wire and for a  $L = 500\text{nm}$  wire in absence of tip potential. Only the right half is shown, as the plot is symmetric about  $x = 0$ . We rescale the  $x$  and  $\rho(x)$  with wire length  $L$  to ease the comparison.

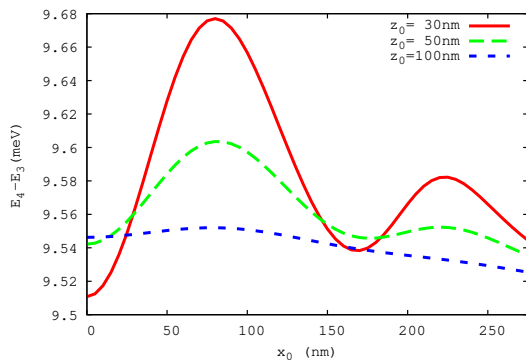


FIG. 4: (Color Online) Coulomb blockade micrographs for a 1D dot with  $L = 500\text{nm}$  and tip charge  $q = 0.02e$  for three tip potentials shown in Fig. 2. Again, the right half is shown.

sity  $\rho^* \approx 35\mu\text{m}^{-1}$ . A Wigner crystallized density variation is shown in the green curve of Fig. 3 for a quantum dot of  $L = 500\text{nm}$ , whereas for  $L = 110$  the four electron density exhibits Friedel oscillations.

Now we introduce a weak tip potential, corresponding to a negatively charged tip of strength  $q = 0.02e$ , scanning above the center axis of the quantum wire along its direction  $(1, 0, 0)$ , with the tip location vector  $\vec{r}_0 = (x_0, 0, z_0)$ . For a 1D quantum dot of length  $L = 500\text{nm}$ , which as shown in Fig. 3 has  $4k_F$  Wigner-crystal density variation, let us consider the three tip heights above the quantum wire,  $z_0 = 30\text{nm}, 50\text{nm}, 100\text{nm}$ , corresponding to the three tip potentials shown in Fig. 2. The resulting Coulomb blockade peak position  $\Delta E$  as a function of the tip coordinate  $x_0$  along the wire, i.e. the Coulomb blockade micrograph, is shown in Fig. 4. Clearly, in Fig. 2 the closer the tip approaches the wire, the more localized is the tip potential and a sharper tip potential make it easier to resolve the density variations, this is reflected in Coulomb blockade micrograph scans in Fig. 4. At  $z_0 = 30\text{nm}, 50\text{nm}$  from the tip to the center of the wire, the  $4k_F$  density oscillation of the quasi-Wigner crystal state on the right can be detected in the

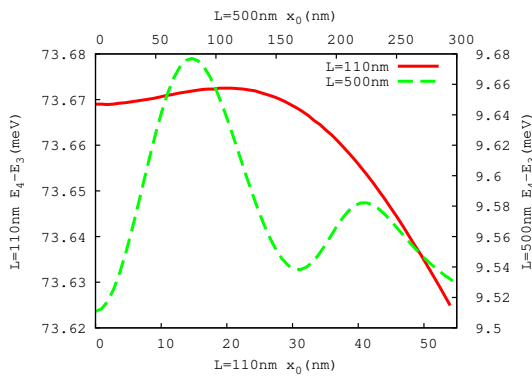


FIG. 5: (Color Online)  $q = 0.02e$  weak tip Coulomb blockade micrographs for densities shown in Fig. 3. The tip distance to the wire is  $z_0 = 30nm$ . Only the right half is shown.

Coulomb blockade micrograph, whereas when  $z_0 = 100nm$  away, the tip potential becomes much too broad to resolve the fine features of the density oscillations. We note that although the resolution of the tip is largely determined by the distance  $z_0$ , the contrast of a Coulomb blockade micrograph, i.e. the magnitude of the  $4k_F$  variations in the micrographs, can be improved by modestly increasing the tip potential.

By contrast, in Fig. 5 the  $L = 110nm$  micrograph at  $z_0 = 30nm$  does not show features of Wigner crystal oscillations. However, this micrograph does not by itself give a clearcut indication of the absence of Wigner crystal order for  $L = 110nm$ . With the current interaction and tip parameters, one cannot observe the crossover from the Wigner crystal to the Friedel oscillations because it happens at a inter-particle spacing  $\Delta x \approx 30nm$ , below the resolution of the micrograph even at  $z = 30nm$ . If the magnitude of the Coulomb repulsion is artificially reduced so that the crossover occurs at  $L = 250nm$ , we find that Coulomb blockade micrograph could unambiguously distinguish the liquid state from the crystal state. Experimentally, one might be able to accomplish this reduction by replacing the  $SiO_x$  layer with a material with higher  $\epsilon$  such as  $HfO_2$ , and by reducing the thickness of this layer, thus bring the screening layer of doped silicon closer to the wire.

To gain a more intuitive understanding of a weak tip Coulomb blockade micrograph, we observe that a weak tip only slightly disturbs the electron density as it scans across the wire, thus, a simple first order perturbation theory should be a good approximation to compute the ground state energy in the presence of the tip potential:

$$E(\vec{r}, q) - E_0(\vec{r}, q) = \int dx V(\vec{r}_0; q, x) \rho(x), \quad (2)$$

where  $\rho(x)$  is the non-interacting ground state density and  $E_0(\vec{r}_0, q)$  is its energy. We have checked that for tip charges up to  $q = 0.1e$  the simple first order perturbation theory gives a decent fit to both the ground state energy and the Coulomb blockade micrograph. Since both the width and the center location of the tip potential  $V(\vec{r}_0; q, x)$  can be adjusted experimentally, the Coulomb blockade microscopy with a weak tip

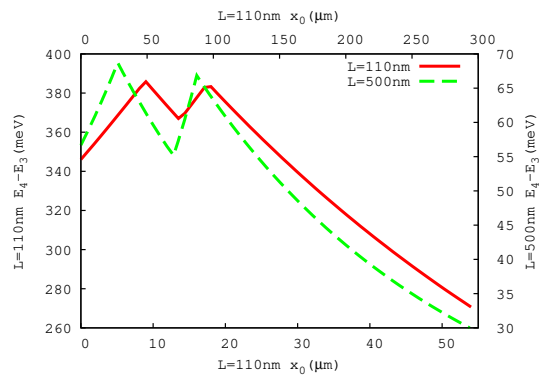


FIG. 6: (Color Online)  $q = 24e$  strong tip limit for the  $N = 3$  to  $N = 4$  Coulomb blockade transition for wire of length  $110nm$  and  $500nm$ . Only the right half is scanned.

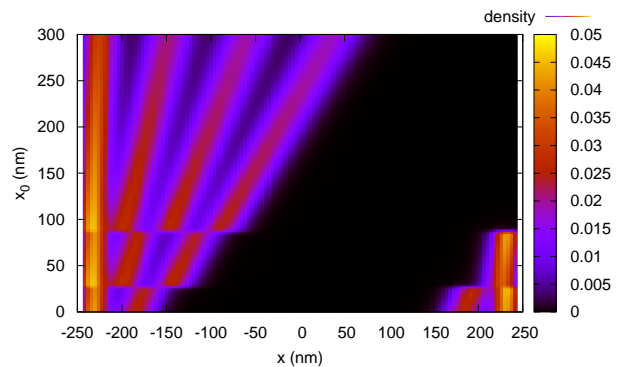


FIG. 7: Electronic densities in  $L = 500nm$ ,  $N = 4$  quantum wire as a tip  $q = 24e$  scan through  $x_0 \leq 250nm$ . The density throughout the entire wire  $-250nm \leq x \leq 250nm$  is shown.

potential provides a flexible way to map the electronic densities in a quantum dot.

In the opposite limit of strong tip, the Coulomb blockade tip scans present a very different physical picture. In Fig. 6 we observe that irrespective of whether the electronic state is liquid or Wigner-crystal like as shown in Fig. 3, the Coulomb blockade micrographs show similar behavior: in the case of  $N = 3$  to  $N = 4$  transition, both the  $L = 110nm$  and  $L = 500nm$  wire show two relatively sharp peaks for a large tip charge  $q = 24$ . This is in contrast with the case of a weak tip Fig. 5, where the Coulomb blockade micrographs show smooth spatial dependence as well as sensitivity to the electronic states in the absence of the tip potential.

To understand the physics of this strong tip limit we note that the two sharp cusps in Fig. 6 represents discontinuous slope changes in the  $N = 4$  electron ground state energy as a function of tip position  $x_0$ . Similarly the deep valley in the figure corresponds to a cusp in  $N = 3$  ground state energy. The origin of these three discontinuities in slopes can be seen in

Fig. 7. In our limit, the negatively charged tip potential is so strong that it depletes the electronic density under it. Thus the tip creates an effective partition of the electrons in the wire into left and right sub-quantum dot. As shown in Fig. 7, as the tip move from the center to right of the wire with four electrons, the partitions of the electrons undergoes two abrupt transitions  $(2, 2) \rightarrow (3, 1) \rightarrow (4, 0)$ . These two transitions correspond to the two cusps shown in the  $N = 4$  curve in Fig. 6. Similarly, the discontinuous slope change shown on the  $N = 3$  curve of the same figure corresponds to the transition between the  $(2, 1) \rightarrow (3, 0)$  partition of the ground state. Thus the three discontinuities seen in the Coulomb blockade micrographs in Fig. 6 correspond to, alternately, the transitions between the integer partitioning of total electron numbers in the  $N = 3$  and  $N = 4$  system.

To better understand the transitions between different partitions, let us consider the transitions in a model of  $N = 4$  electrons, with spin, which have no Coulomb repulsion between them but interact with a repulsive tip potential. When tip is at the center of the wire, the electrons are partitioned  $(2, 2)$  and both electrons in each side reside in the single-particle ground state. As the tip moves rightward, the energy levels rise in the right partition and fall in the left. When the first excited level on the left partition crosses the ground state on the right, *all* electrons will move to the left partition. Therefore, contrary to the interacting case, there is no energetically favorable state of  $(3, 1)$  partitioning in the non-interacting system. In the  $N = 3$  case, the  $(2, 1)$  partition is not affected by this, and for non-interacting system the transition  $(2, 1) \rightarrow (3, 0)$  will coincide with the transition in  $N = 4$ , so the Coulomb blockade micrograph will show only a single peak. This analysis can also be generalized to a wire containing multiple non-interacting electrons, such that the all the  $(odd, odd)$  partitionings of electron number will be missing.

With the non-interacting case in mind, we postulate that the distance between two peaks in  $N = 3$  to  $N = 4$  micrographs, corresponding to the tip positions where  $(3, 1)$  partitioning in the  $N = 4$  wire is stable, can serve as an indicator of the relative importance of the interaction energy versus the sum of kinetic and single particle potential energies. With interaction, the one and two electron state in each partition would not be degenerate, and the  $(3, 1)$  partition can survive. But the less important interaction is compared to single particle energies, the less splitting would the one and two particle energies be, and the smaller is the region of stable  $(3, 1)$  partition. This can be seen in Fig. 6. The potential energy should have a larger share in the total energy in the longer wire with lower electronic density, and indeed we observe that the longer wire has a wider distance between the two peaks marking  $(2, 2) \rightarrow (3, 1)$  and  $(3, 1) \rightarrow (4, 0)$  transitions.

Beyond the system of interacting electrons discussed above,

a possible further application of Coulomb blockade microscopy is to experimentally “map” the rugged potential landscape produced by wire inhomogeneities and charged impurities in the substrate. One would focus on the transition from  $N = 0$  to  $N = 1$  state, in which case the Coulomb blockade micrograph would reveal information about the single particle density. By inverting the transformation in Eq. 2, one may be able to approximately obtain the single particle ground state density  $\rho(x)$ . In the absence of an external magnetic field, the ground state wavefunction  $\psi(x)$  has no nodes and can be chosen to be  $\psi(x) = (\rho(x))^{1/2}$ . It is then straightforward to invert the Schrödinger’s equation to extract the potential landscape from the single particle wavefunction.

In summary, in this paper we show that tracking the peak position shift as a charged mobile tip move above and across a nanowire, a technique we term Coulomb blockade microscopy, can reveal spatially-resolved information about the electronic density and states of a quantum 1D dot. A weak tip potential can serve as a probe with tunable a width, to reveal the spatial distribution of the electronic density in the wire. A strong tip potential that depletes part of the wire can be used to manipulate individual electrons from one partition to the other, and the accompanying Coulomb blockade micrograph can indicate the transitions between different partitionings. Furthermore, a feature of the resulting micrograph, the distance between peaks marking the  $(odd, odd)$  partitioning, can serve as an indicator of the relative strength of the interaction. In this paper we have chosen extreme values of the tip charge  $q$  to illustrate the physics in the two limits. However, our calculations show that the discussions above hold true for a wider range of moderately small and large values of  $q$ .

We would like to thank Erin Boyd, Halvar Trodahl and Jesse Berezovsky and especially Bob Westervelt for helpful discussions. This work is supported in part by NSF grants PHY-0646094 and DMR-0541988. Numerical work was performed in part at the Center for Nanoscale Systems, a member of the National Nanotechnology Infrastructure Network (NNIN) supported by NSF award ECS-0335765.

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